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# HL6314MG

AlGaInP Laser Diode

# HITACHI

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## Description

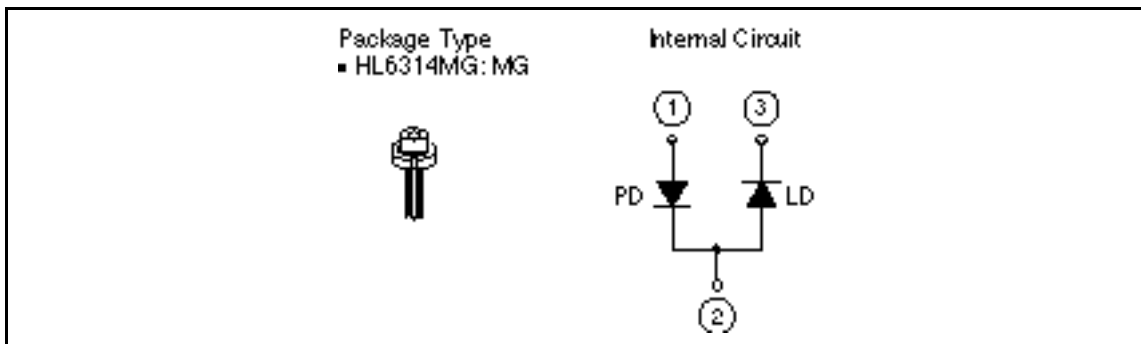
The HL6314MG is a 0.63  $\mu\text{m}$  band AlGaInP laser diode with a multi-quantum well (MQW) structure. It is suitable as a light source for laser pointers and optical equipment for amusement.

## Application

- Laser pointer

## Features

- Visible light output: 635nm Typ (nearly equal to He-Ne gas laser)
- Optical output power: 3 mW CW
- Low operating current: 30 mA Typ
- Low operating voltage: 2.7 V Max



## HL6314MG

### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ )

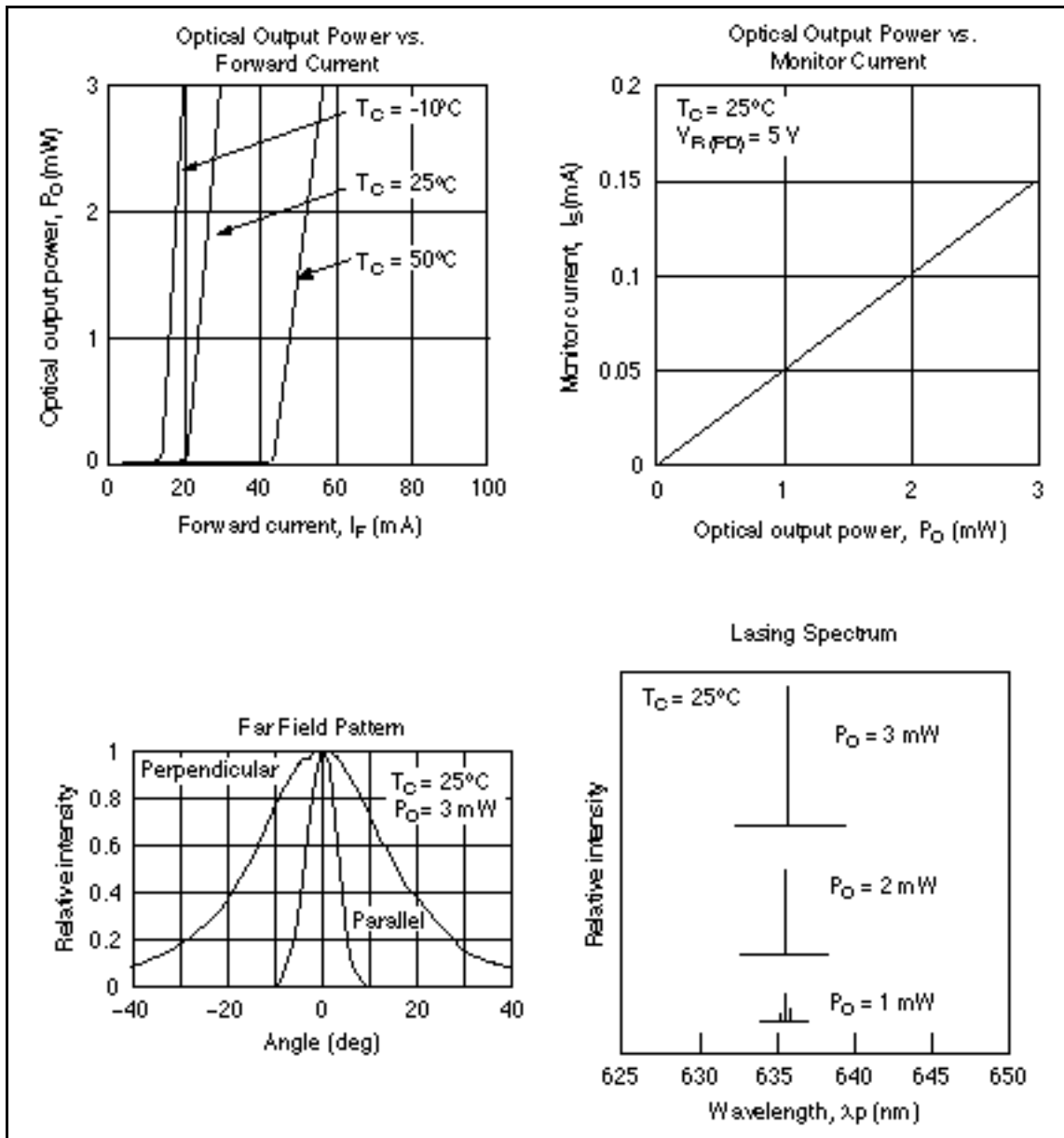
Item	Symbol	Rated Value	Unit
Optical output power	$P_O$	3	mW
Pulse optical output power	$P_{O(\text{pulse})}$	5* <sup>1</sup>	mW
LD reverse voltage	$V_{R(\text{LD})}$	2	V
PD reverse voltage	$V_{R(\text{PD})}$	30	V
Operating temperature	$T_{opr}$	-10 to +50	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +85	$^\circ\text{C}$

Note: 1. Pulse condition: Pulse width 1 $\mu\text{s}$ , duty 50%

### Optical and Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

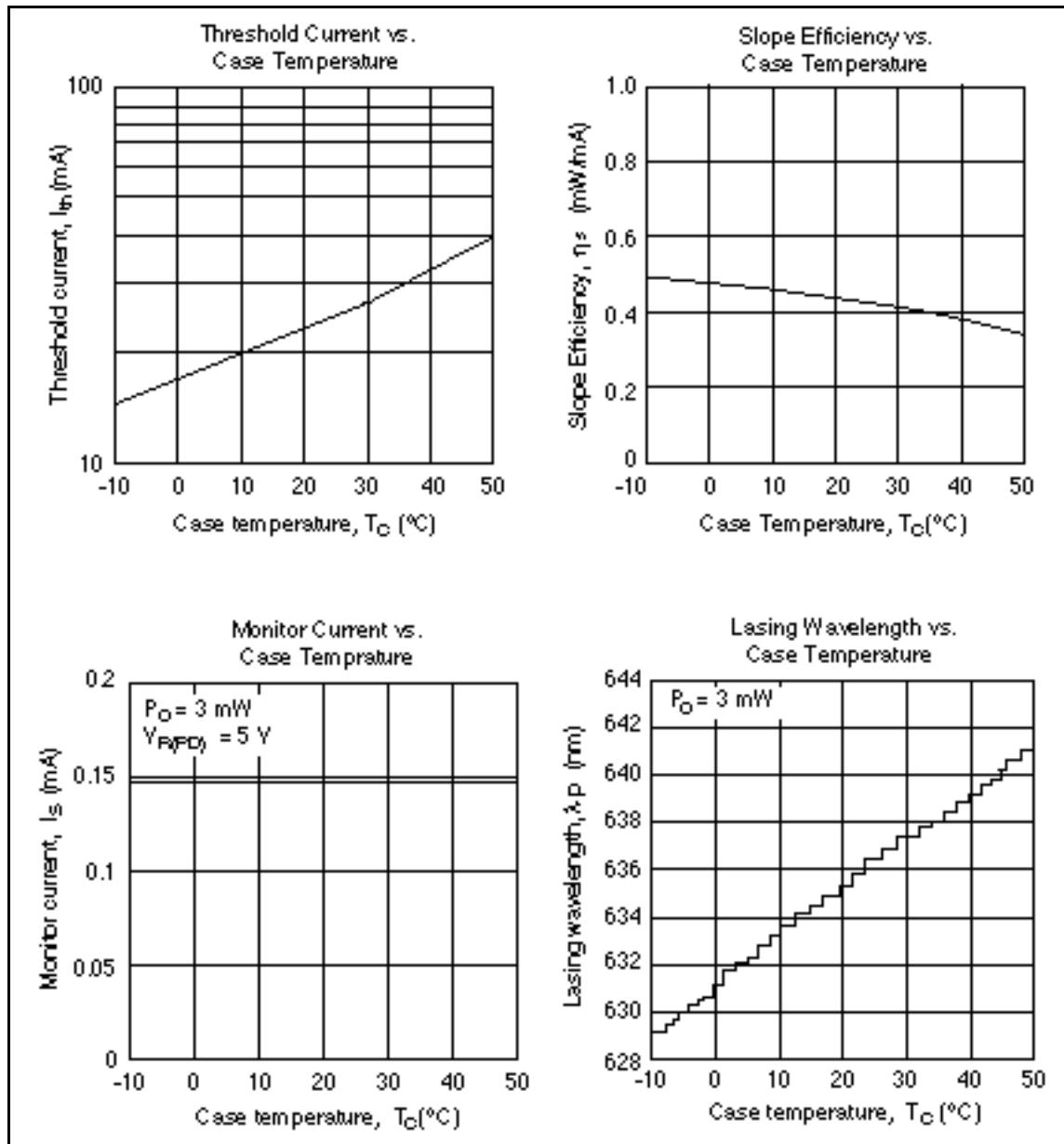
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Optical output power	$P_O$	3	—	—	mW	Kink free
Threshold current	$I_{th}$	—	25	35	mA	
Operating current	$I_{op}$	—	30	42	mA	$P_O = 3 \text{ mW}$
Operating voltage	$V_{op}$	—	—	2.7	V	$P_O = 3 \text{ mW}$
Lasing wavelength	$\lambda$	630	635	640	nm	$P_O = 3 \text{ mW}$
Beam divergence (parallel)	//	6	8	10	deg.	$P_O = 3 \text{ mW}$
Beam divergence (perpendicular)		23	30	39	deg.	$P_O = 3 \text{ mW}$
Monitor current	$I_s$	0.08	0.15	0.4	mA	$P_O = 3 \text{ mW}, V_{R(\text{PD})} = 5 \text{ V}$

Typical Characteristic Curves

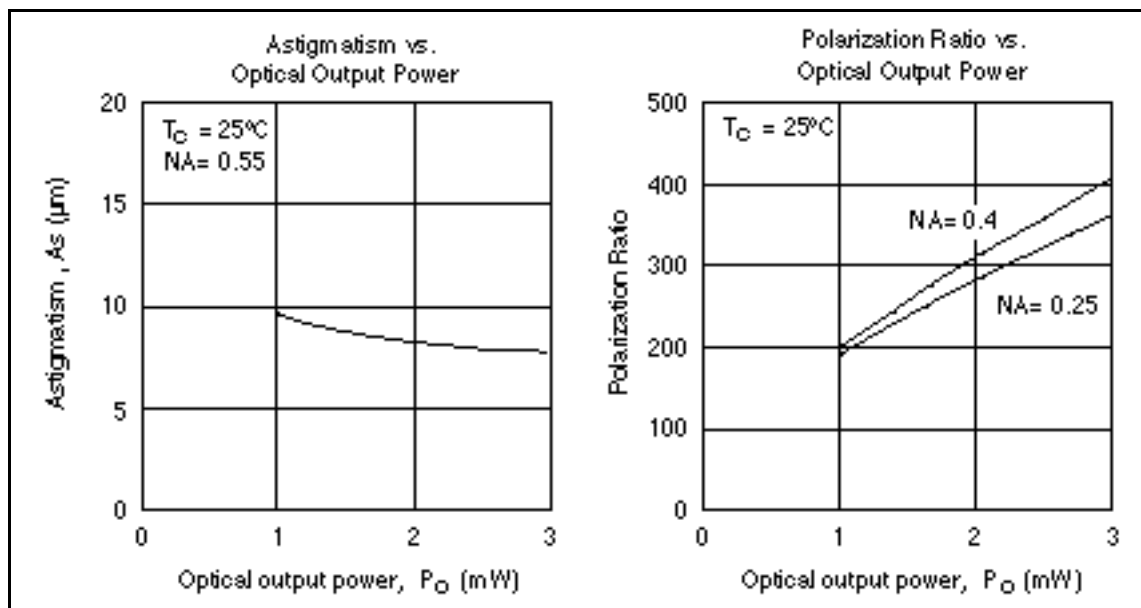


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## Typical Characteristic Curves (cont)



Typical Characteristic Curves (cont)



**Polarization direction**

The polarization direction is TM mode. The polarization of 0.63  $\mu\text{m}$  LD's is different from that of 0.83/0.78/0.67  $\mu\text{m}$  LD's. The polarization direction of 0.63  $\mu\text{m}$  LD's is illustrated in the figure below

